

PHASE CONTROL THYRISTORS

■ Junction Size	: Square 340 mils - IR343SG12H/ S1233
■ Wafer Size	: 4"
■ V_{RRM}/V_{DRM} Class	: 1200 V
■ Passivation Process	: Glassivated MESA
■ Reference IR Packaged Part	: 50RIA Series

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{TM} Typical On-state Voltage	1.2 V	$T_J = 25^\circ\text{C}$, $I_T = 25\text{ A}$
V_{RRM}/V_{DRM} Direct and Reverse Breakdown Voltage	1200 V	$T_J = 25^\circ\text{C}$, $I_{DRM}/I_{RRM} = 100\ \mu\text{A}$ (1)
I_{GT} Required DC Gate Current to Trigger	5 to 100 mA	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
V_{GT} Max. Required DC Gate Voltage to Trigger	2 V	$T_J = 25^\circ\text{C}$, anode supply = 6 V, resistive load
I_H Holding Current Range	5 to 200 mA	Anode supply = 6 V, resistive load
I_L Maximum Latching Current	400 mA	Anode supply = 6 V, resistive load

(1) Nitrogen flow on die edge.

Mechanical Characteristics

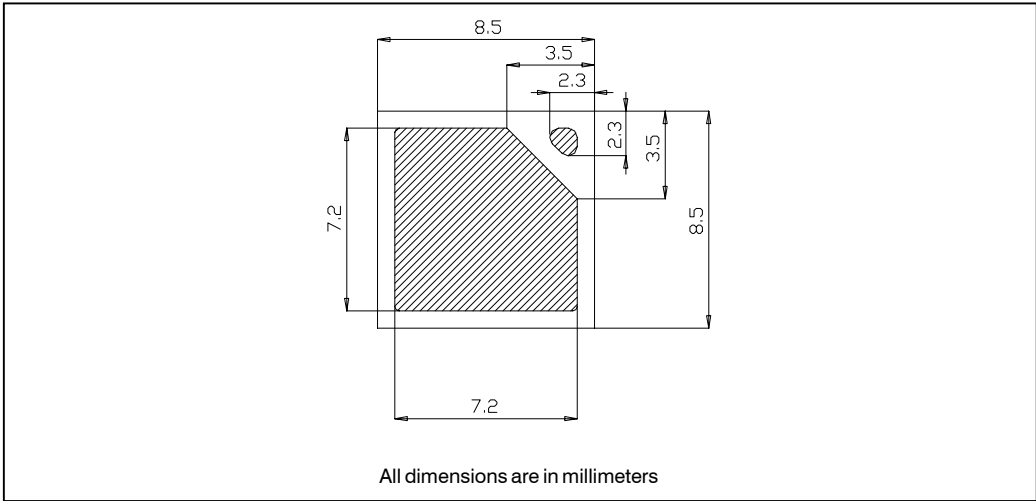
Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Nominal Front Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 15 KA)
Chip Dimensions	340x340 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	$330\ \mu\text{m} \pm 10\ \mu\text{m}$
Maximum Width of Sawing Line	$130\ \mu\text{m}$
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

S1233

Bulletin I0142J 01/01

International
IRF Rectifier

Outline Table



Wafer Layout

